

ABSTRACT OF THE DISCLOSURE

ANNEALING PROCESS AND DEVICE OF SEMICONDUCTOR WAFER

5 A device and method for annealing a wafer. The preferred embodiment includes applying a basic thermal budget to a weakened zone of a wafer, substantially evenly over the weakened zone. The basic thermal budget is insufficient to detach a detachment layer from a remainder of the wafer at the weakened zone. An additional thermal budget is applied locally in an initiation region of the weakened zone to initiate the detachment of the detachment layer at the weakened zone.